

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	_	,		•			
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{DS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 100			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 2.5		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V			- 1		
		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50	μΑ	
		V <sub>DS</sub> = - 100 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			- 250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 15			Α	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.6 A	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.6 A 0.162 0.195   V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.4 A 0.175 0.210				
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.4 A			0.210	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 3.6 A		12		S	
Dynamic <sup>b</sup>	•			•			
Input Capacitance	C <sub>iss</sub>			1055		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -50 \text{ V}, f = 1 \text{ MHz}$		65			
Reverse Transfer Capacitance	C <sub>rss</sub>	1		41			
Total Gate Charge <sup>c</sup>	Q <sub>g</sub>	V <sub>DS</sub> = - 50 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 3.6 A		23.2	34.8		
				11.7	17.6	nC	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = -50 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -3.6 \text{ A}$		3.5			
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			4.8			
Gate Resistance	$R_g$	f = 1 MHz	1.2	5.7	11.5	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			7	14	- ns	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -50 \text{ V}, R_{L} = 17.2 \Omega$		12	18		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong$ - 2.9 A, $V_{GEN}$ = - 10 V, $R_g$ = 1 $\Omega$		33	50		
Fall Time <sup>c</sup>	t <sub>f</sub>	]		9	18		
Drain-Source Body Diode Ratings at	nd Characteri	istics T <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	I <sub>S</sub>				- 8.8	А	
Pulsed Current	I <sub>SM</sub>				- 15		
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 2.9 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.5	٧	
Reverse Recovery Time	t <sub>rr</sub>			50	75	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = - 2.9 A, dl/dt = 100 A/μs		- 4	- 6	Α	
Reverse Recovery Charge	Q <sub>rr</sub>	1		98	147	nC	

#### Notes:

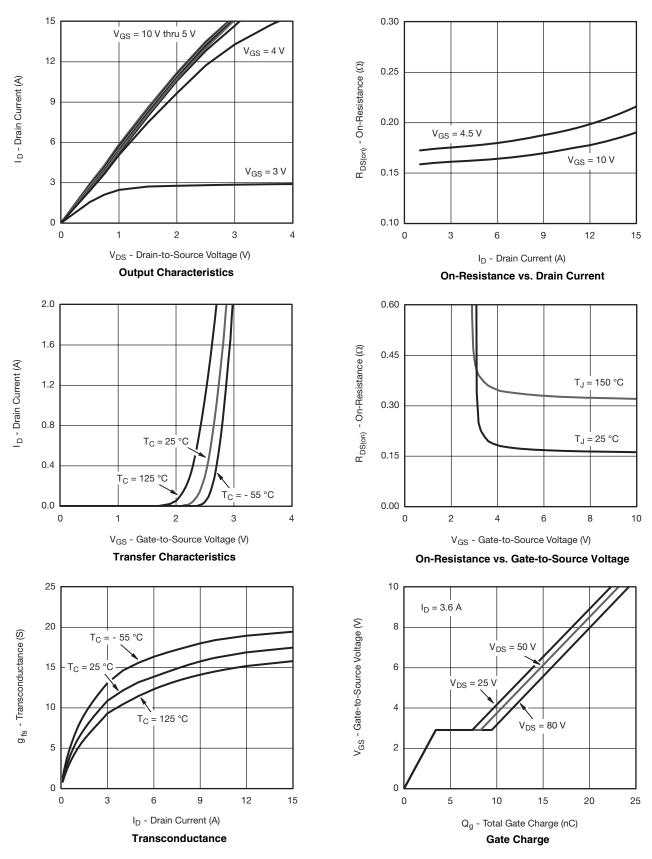
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



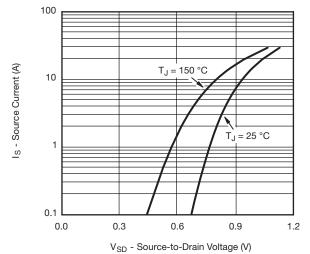


#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

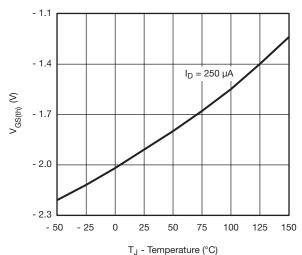


# VISHAY

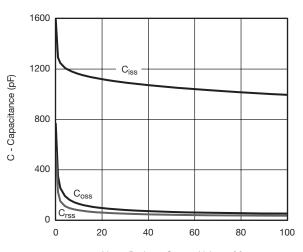
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



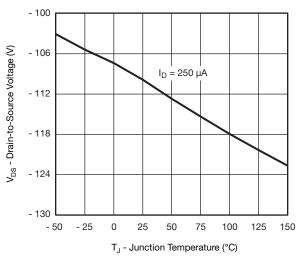
Source-Drain Diode Forward Voltage



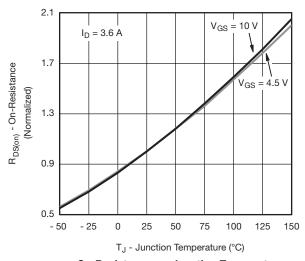
Threshold Voltage



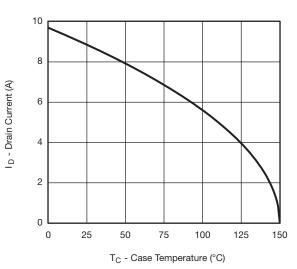
 $V_{DS}$  - Drain-to-Source Voltage (V)  $\label{eq:capacitance}$ 



**Drain Source Breakdown vs. Junction Temperature** 



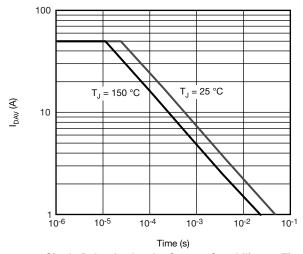
On-Resistance vs. Junction Temperature

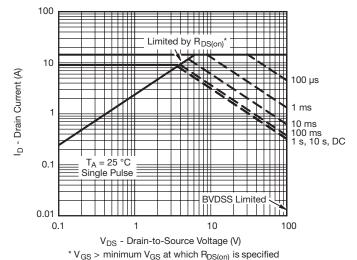


**Current Derating** 

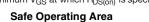


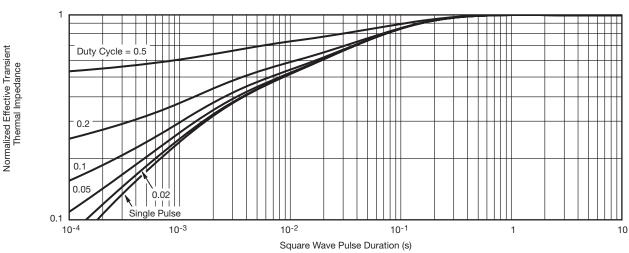
#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Avalanche Current Capability vs. Time



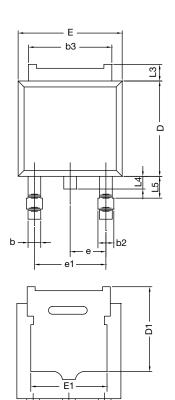


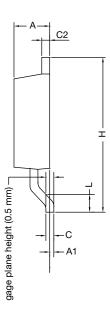
Normalized Thermal Transient Impedance, Junction-to-Case

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## **TO-252AA Case Outline**





	MILLIN	METERS	INCHES				
DIM.	MIN.	MAX.	MIN.	MAX.			
Α	2.18	2.38	0.086	0.094			
A1	-	0.127	-	0.005			
b	0.64	0.88	0.025	0.035			
b2	0.76	1.14	0.030	0.045			
b3	4.95	5.46	0.195	0.215			
С	0.46	0.61	0.018	0.024			
C2	0.46	0.89	0.018	0.035			
D	5.97	6.22	0.235	0.245			
D1	4.10	-	0.161	-			
Е	6.35	6.73	0.250	0.265			
E1	4.32	-	0.170	-			
Н	9.40	10.41	0.370	0.410			
е	2.28 BSC		0.090 BSC				
e1	4.56 BSC		0.180 BSC				
L	1.40	1.78	0.055	0.070			
L3	0.89	1.27	0.035	0.050			
L4	-	1.02	-	0.040			
L5	1.01	1.52	0.040	0.060			
ECN: T16-0236-Rev. P, 16-May-16							

#### DWG: 5347 Notes

• Dimension L3 is for reference only.

Revision: 16-May-16 Document Number: 71197



#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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